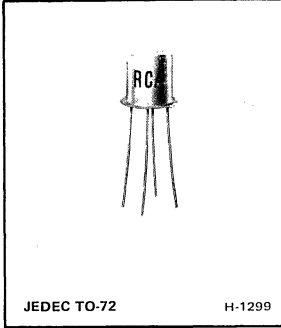


**RCA**  
Solid State  
Division

# RF Power Transistors

## 2N3478



### SILICON N-P-N EPITAXIAL PLANAR TRANSISTOR

For VHF/UHF Applications  
in Industrial and Commercial Equipment

**Features:**

- high gain-bandwidth product –  $f_T = 900\text{ MHz typ.}$
- low noise figure  
 $NF = 5\text{ dB typ. at } 470\text{ MHz}$   
 $4.5\text{ dB max. at } 200\text{ MHz}$   
 $2.5\text{ dB typ. at } 60\text{ MHz}$
- high unneutralized power gain  
 $G_{pe} = 11.5\text{ dB min. at } 200\text{ MHz}$
- hermetically sealed four-lead package
- all active elements insulated from case
- low collector-to-base feedback capacitance,  $C_{cb} 0.7\text{ pF max.}$

RCA-2N3478 is an epitaxial planar transistor of the silicon n-p-n type with characteristics which make it extremely useful as a general purpose rf amplifier at frequencies up to 470MHz. These characteristics include an exceptionally low noise figure at high frequencies, low leakage current, and a high gain-bandwidth product.

The 2N3478 utilizes a hermetically sealed four-lead package in which active elements of the transistor are insulated from the case. The case may be grounded by means of a fourth lead in applications requiring minimum feedback capacitance, shielding of the device, or both.

**TERMINAL CONNECTIONS**

- Lead 1 – Emitter
- Lead 2 – Base
- Lead 3 – Collector
- Lead 4 – Connected to case

**Maximum Ratings, Absolute-Maximum Values:**

Collector-to-Base Voltage, $V_{CBO}$ .....	30 max.	V
Collector-to-Emitter Voltage, $V_{CEO}$ .....	15 max.	V
Emitter-to-Base Voltage, $V_{EBO}$ .....	2 max.	V
Collector Current, $I_C$ .....	limited by dissipation	

**Transistor Dissipation,  $P_T$ :**

at ambient } up to 25° C . . . . .	200 max.	mW
temperatures } above 25° C . . . . .		See Fig. 1

**Temperature Range:**

Storage and Operating (Junction)	-65 to 200	°C
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**Lead Temperature (During Soldering):**

At distances not closer than 1/32" to seating surface for 10 seconds max. . . . .	265 max.	°C
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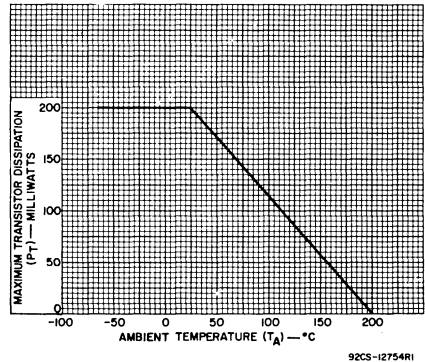


Fig. 1 - Rating chart for type 2N3478

ELECTRICAL CHARACTERISTICS, At an Ambient Temperature, ( $T_A$ ) of 25° C

Characteristics	Symbols	TEST CONDITIONS			LIMITS			Units
		Frequency f	DC Collector- to-Emitter Voltage V <sub>CE</sub>	DC Collector Current I <sub>C</sub>	Type 2N3478			
					Min.	Typ.	Max.	
		MHz	V	mA				
Collector-Cutoff Current ( $V_{CB} = 1 \text{ V}, I_E = 0$ )	$I_{CBO}$				-	-	0.02	$\mu\text{A}$
Collector-to-Base Breakdown Voltage ( $I_E = 0$ )	$BV_{CBO}$			0.001	30	-	-	V
Collector-to-Emitter Breakdown Voltage	$BV_{CEO}$			0.001	15	-	-	V
Emitter-to-Base Breakdown Voltage ( $I_E = -0.001 \text{ mA}$ )	$BV_{EBO}$			0	2	-	-	V
Static Forward-Current Transfer Ratio	$h_{FE}$		8	2	25	-	150	
Magnitude of Small-Signal Forward-Current Transfer Ratio	$h_{fe}^a$	100	8	2	7.5	9	16	
Collector-to-Base Feedback Capacitance ( $V_{CB} = 10 \text{ V}, I_E = 0$ )	$C_{cb}^b$	0.1 to 1			-	-	0.7	pF
Small-Signal, Common-Emitter Power Gain in Unneutralized Amplifier Circuit (See Fig.4)	$G_{pe}^a$	200	8	2	11.5	-	17	dB
Small-Signal, Common-Emitter Power Gain in Neutralized Amplifier Circuit	$G_{pe}^a, c$	470	6	1.5	-	12	-	dB
UHF Noise Figure	$NF^a, c$	470	6	1.5	-	5	-	dB
VHF Noise Figure (See Fig.4)	$NF^a$ $NF^a, d$	200 60	8 8	2 1	- -	- 2.5	4.5 -	dB dB

<sup>a</sup> Fourth lead (case) grounded.

<sup>b</sup>  $C_{cb}$  is a three terminal measurement of the collector-to-base capacitance with the emitter and case connected to the guard terminal.

<sup>c</sup> Source Resistance,  $R_s = 50 \text{ ohms}$ .

<sup>d</sup> Source Resistance,  $R_s = 400 \text{ ohms}$ .

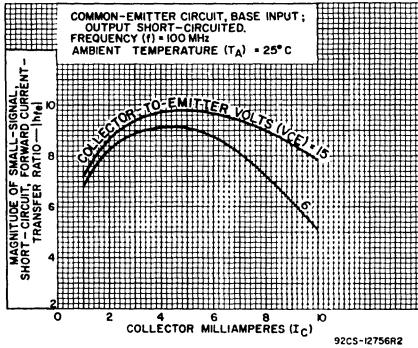


Fig. 2—Typical small-signal beta characteristics for type 2N3478

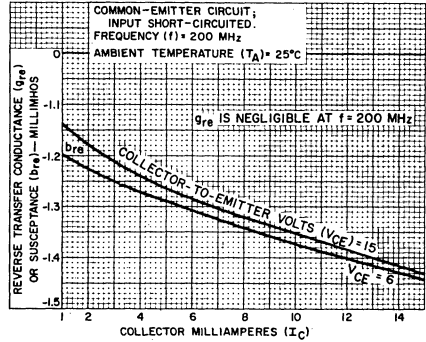
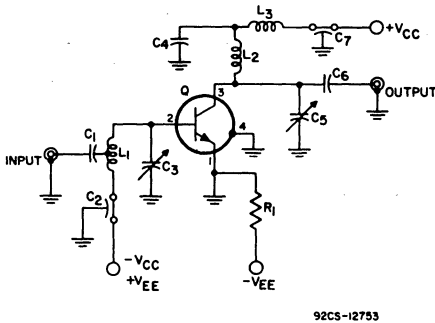


Fig. 3—Reverse transmittance ( $y_{re}$ )



$$C_1, C_4 = 510 \text{ pF}$$

$$C_2, C_7 = 2300 \text{ pF}$$

$$C_3, C_5 = 2\text{-}25 \text{ pF}$$

$$C_6 = 10 \text{ pF}$$

$$R_1 = 2000 \text{ ohms}$$

$$Q = 2N3478$$

$$L_1 = \frac{1}{2} \text{ Turn \# 14 Formvar} \bullet \text{ center tapped}$$

$$\text{Length}_1, l_1 = 2 \text{ inches}$$

$$L_2 = \frac{1}{2} \text{ Turn \# 14 Formvar} \bullet$$

$$\text{Length}_2, l_2 = 1 \frac{1}{2} \text{ inches}$$

$$L_3 = 1 \mu\text{H RRF choke}$$

$$\text{Source (Generator) Resistance}$$

$$R_g = 50 \text{ ohms}$$

$$\text{Load Resistance } R_L = 50 \text{ ohms}$$

• Trademark, Shawindian Products Corporation.

Fig. 4—200 MHz power gain and noise figure test circuit for type 2N3478

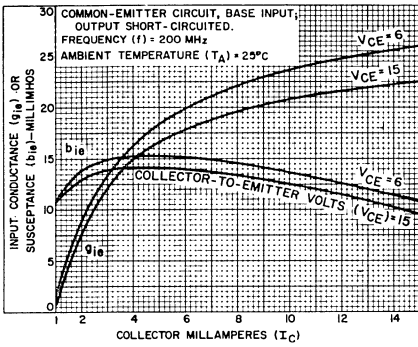


Fig. 5—Input admittance ( $y_{ie}$ )

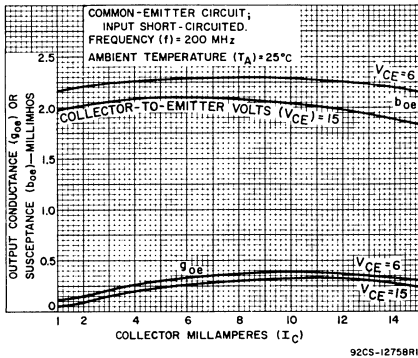


Fig. 6—Output admittance ( $y_{oe}$ )

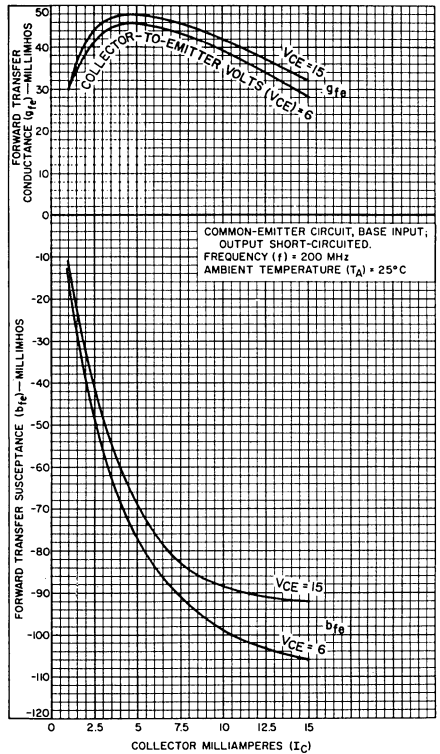


Fig. 7—Forward transmittance ( $y_{fe}$ )

TERMINAL DIAGRAM

Bottom View

